

# EE C245 - ME C218

## Introduction to MEMS Design


### Fall 2012

**Prof. Clark T.-C. Nguyen**

Dept. of Electrical Engineering & Computer Sciences  
University of California at Berkeley  
Berkeley, CA 94720

**Lecture Module 15: Gyros, Noise, & MDS**

EE C245: Introduction to MEMS Design    LecM 15    C. Nguyen    11/18/08    1



## Lecture Outline

- Reading: Senturia, Chpt. 14, Chpt. 16, Chpt. 21
- Lecture Topics:
  - ↳ Gyroscopes
  - ↳ Gyro Circuit Modeling
  - ↳ Minimum Detectable Signal (MDS)
    - Noise
    - Angle Random Walk (ARW)

EE C245: Introduction to MEMS Design    LecM 15    C. Nguyen    11/18/08    2

UC Berkeley

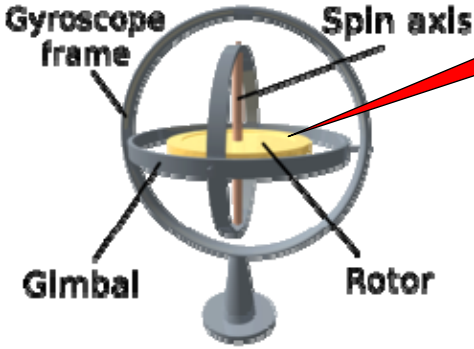
## Gyroscopes

EE C245: Introduction to MEMS Design    LecM 15    C. Nguyen    11/18/08    3


UC Berkeley

### Classic Spinning Gyroscope

- A gyroscope measures rotation rate, which then gives orientation → very important, of course, for navigation
- Principle of operation based on conservation of momentum
- Example: classic spinning gyroscope



Rotor will preserve its angular momentum (i.e., will maintain its axis of spin) despite rotation of its gimbal chassis



EE C245: Introduction to MEMS Design    LecM 15    C. Nguyen    11/18/08    4

## Vibratory Gyroscopes

**UC Berkeley**

- Generate momentum by vibrating structures
- Again, conservation of momentum leads to mechanisms for measuring rotation rate and orientation
- **Example:** vibrating mass in a rotating frame

Mass at rest  $y$   $x$

Driven into vibration along the  $y$ -axis

$y'$   $x'$

$C(t)$

$y$ -displaced mass

Capacitance between mass and frame = constant

Rotate  $30^\circ$

Get an  $x'$  component of motion

$C(t_2) > C(t_1)$

$C(t_1)$

$C(t_2)$

EE C245: Introduction to MEMS Design    LecM 15    C. Nguyen    11/18/08    5

## Basic Vibratory Gyroscope Operation

**UC Berkeley**

### Principle of Operation

- Tuning Fork Gyroscope:

Input Rotation  $\vec{\Omega}$

Driven Vibration @  $f_0$

Coriolis (Sense) Response  $\vec{a}_c$

Coriolis Torque

Side View:

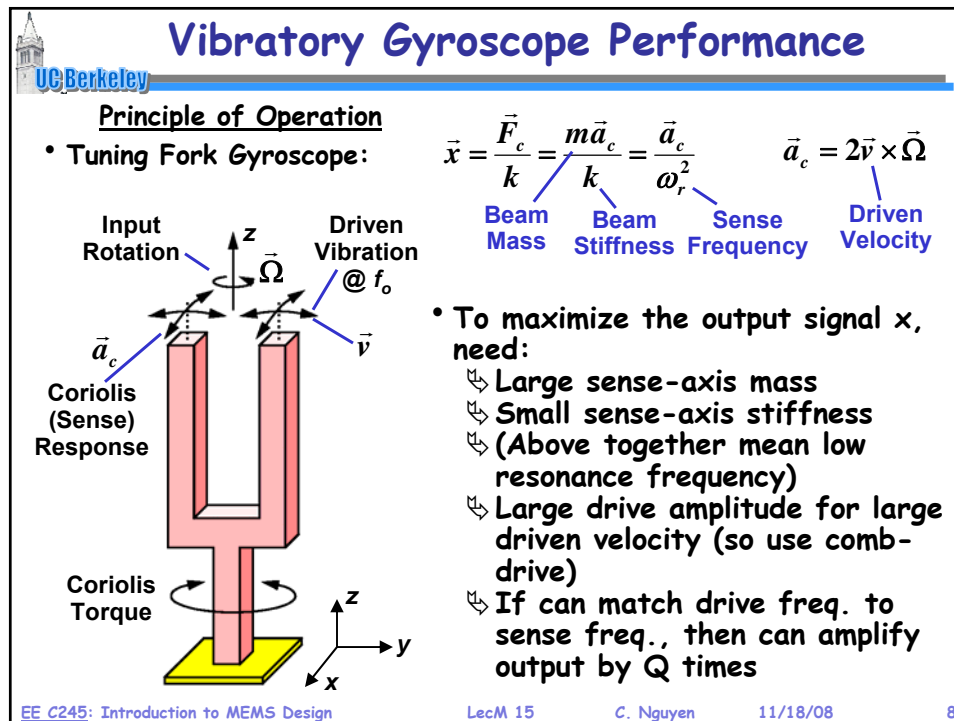
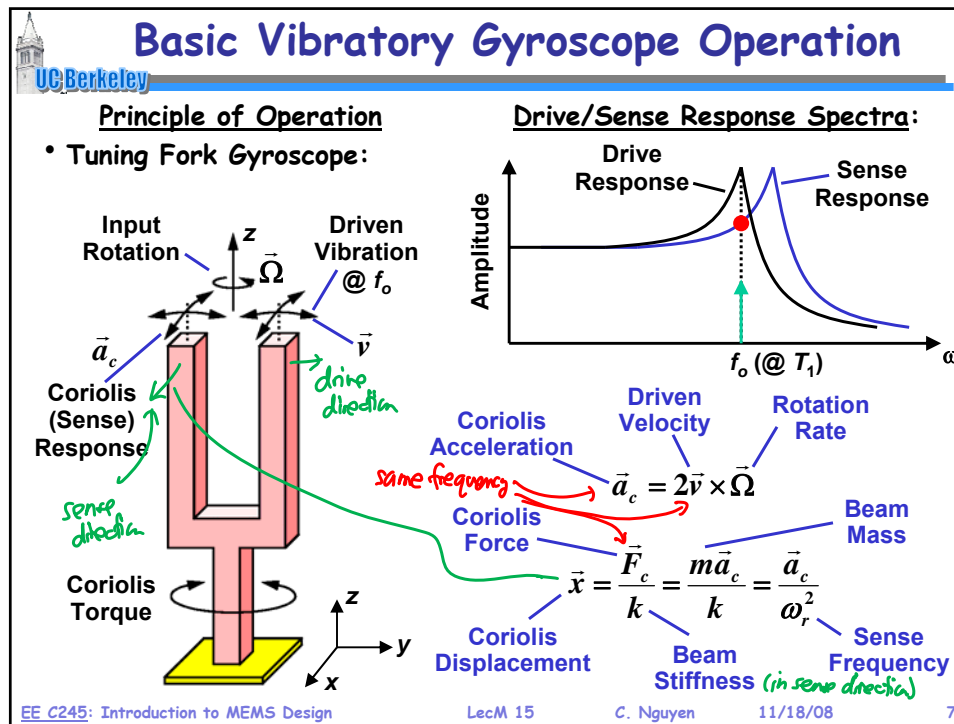
Top View:

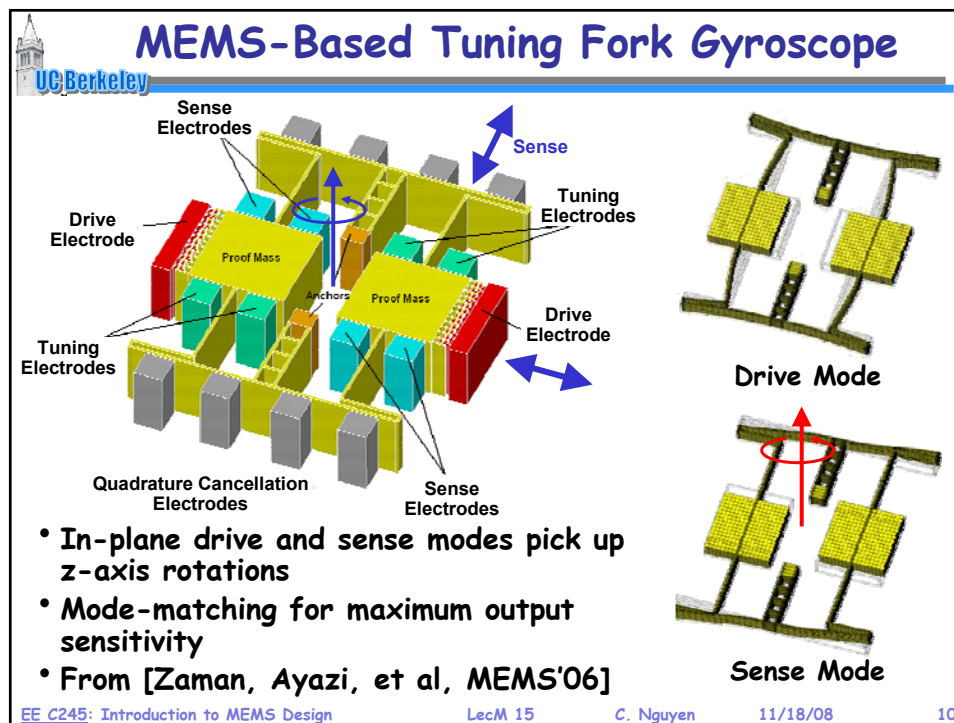
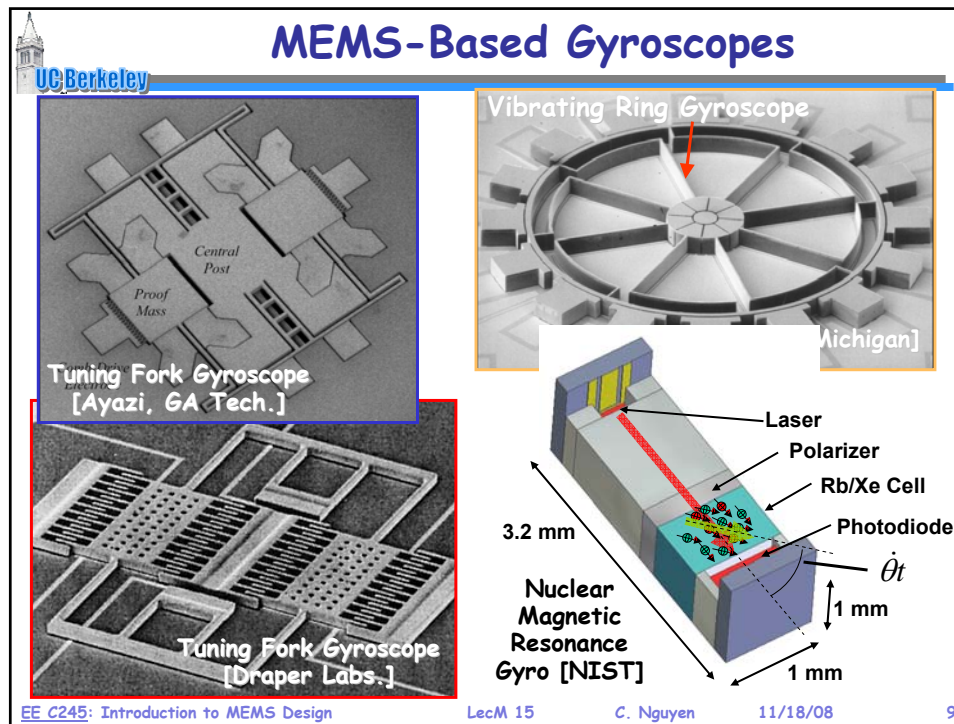
not fore on support support = 0 very little anchor dissipation

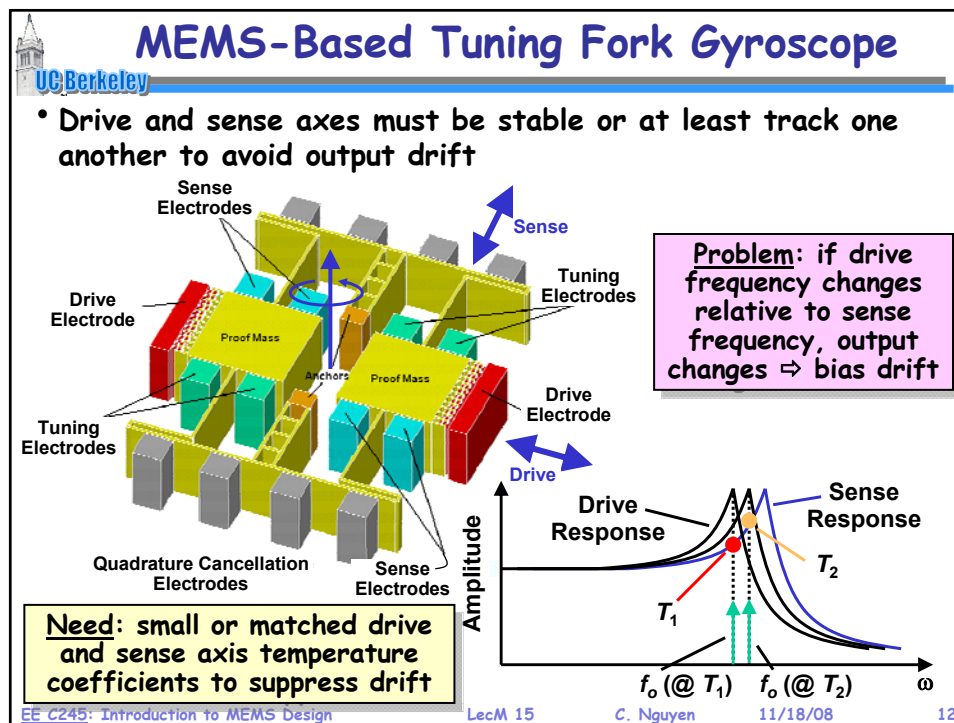
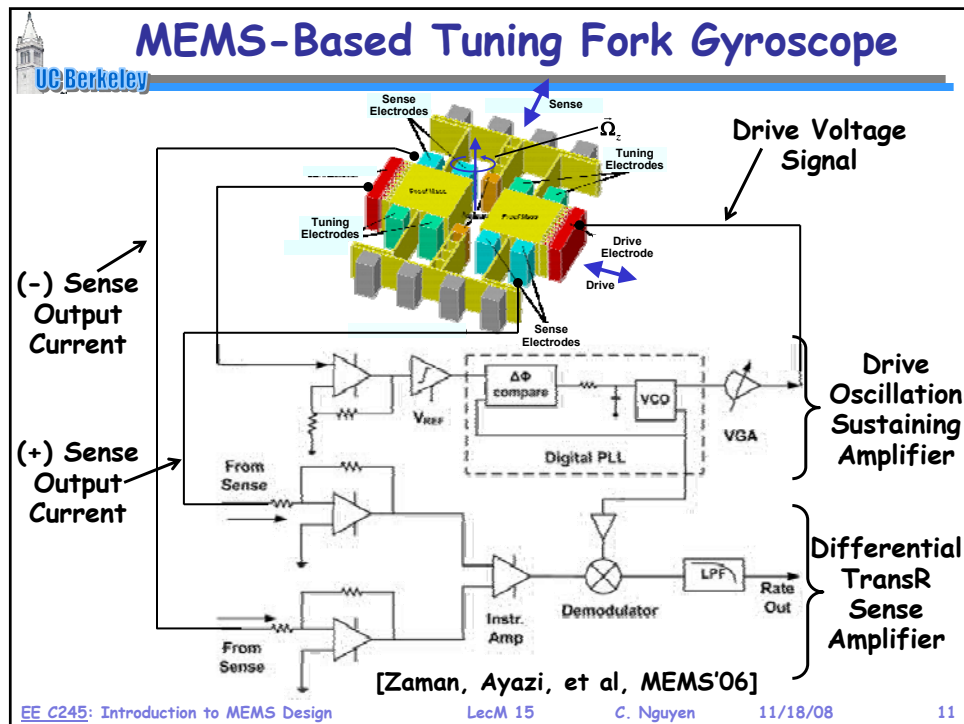
Post

Detect motion out-of-the plane of the tuning fork as rotation!

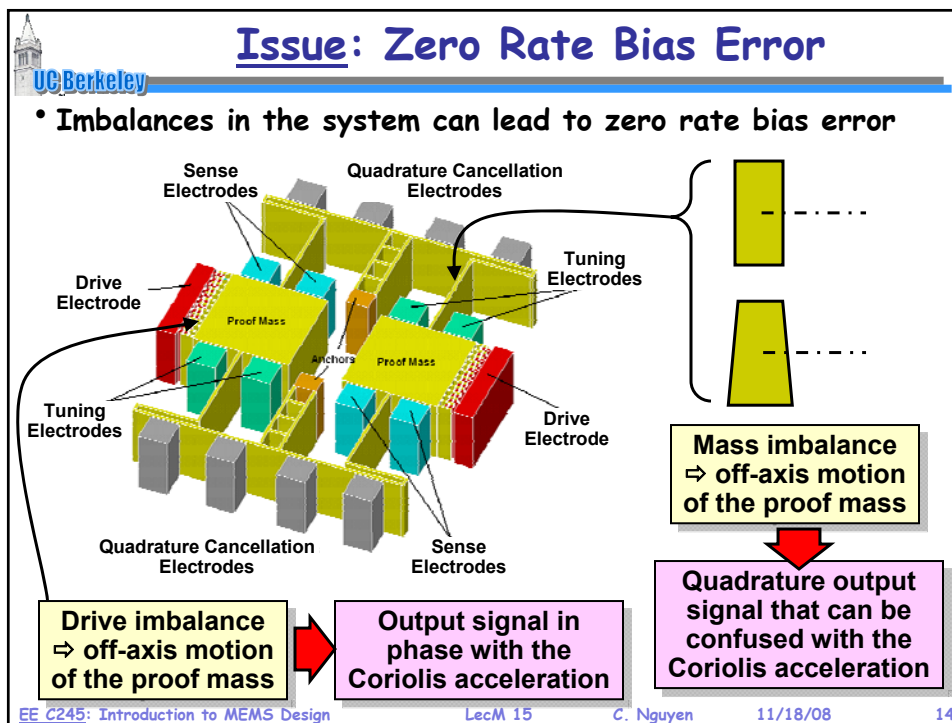
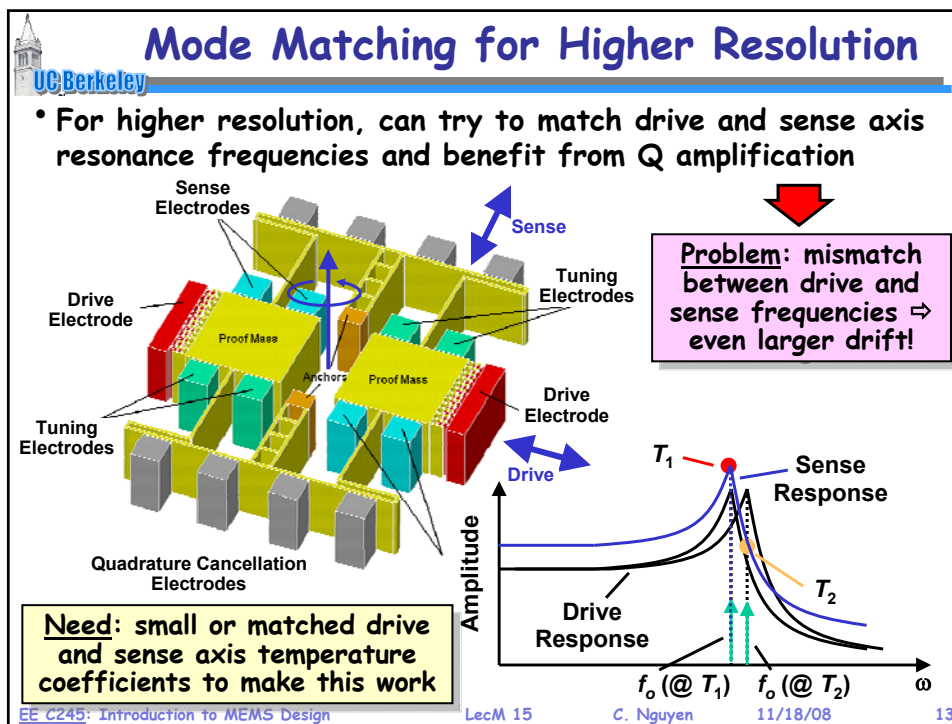
EE C245: Introduction to MEMS Design    LecM 15    C. Nguyen    11/18/08    6











## Nuclear Magnetic Res. Gyroscope

UC Berkeley

- The ultimate in miniaturized spinning gyroscopes?
  - from CSAC, we may now have the technology to do this

Atoms  
Aligned  
Nuclear Spins

Better if this is a noble gas nucleus (rather than e-), since nuclei are heavier  $\Rightarrow$  less susceptible to B field

Soln: Spin polarize Xe<sup>129</sup> nuclei by first polarizing e- of Rb<sup>87</sup> (a la CSAC), then allowing spin exchange

3.2 mm  
1 mm  
1 mm

Challenge: suppressing the effects of B field

EE C245: Introduction to MEMS Design    LecM 15    C. Nguyen    11/18/08    15

## MEMS-Based Tuning Fork Gyroscope

UC Berkeley

Sense Electrodes  
Tuning Electrodes  
Drive Electrode

Drive Voltage Signal

(-) Sense Output Current

(+) Sense Output Current

$\Delta\Phi$  compare  
VCO  
Digital PLL  
VGA  
Demodulator  
Instr. Amp  
Rate Out

Drive Oscillation Sustaining Amplifier

Differential TransR Sense Amplifier

[Zaman, Ayazi, et al, MEMS'06]

EE C245: Introduction to MEMS Design    LecM 15    C. Nguyen    11/18/08    16



## Determining Sensor Resolution

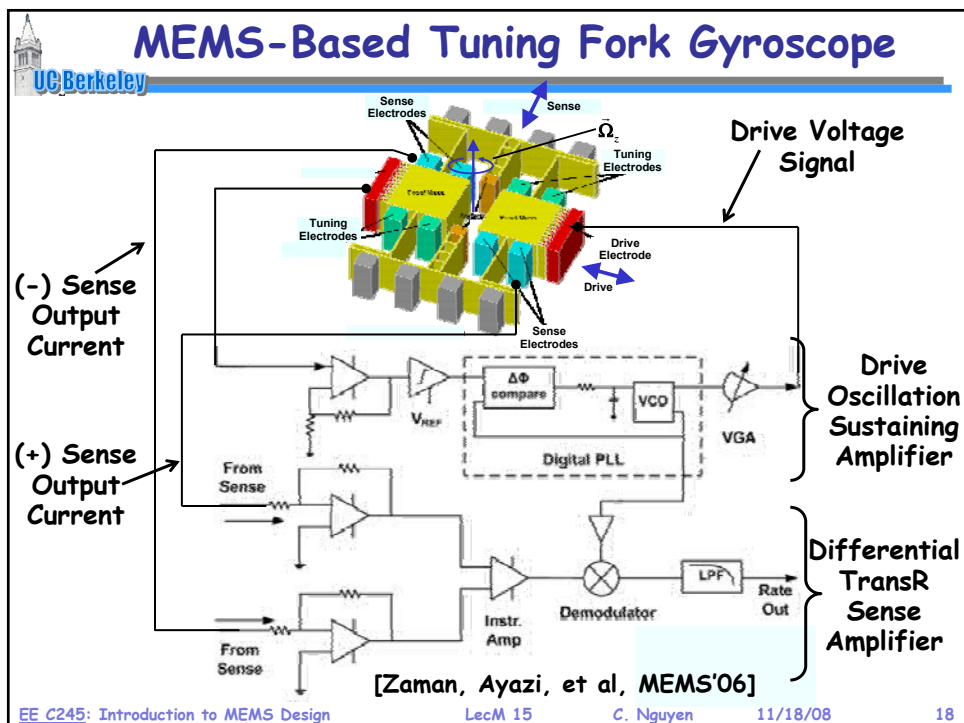
EE C245: Introduction to MEMS Design

LecM 15

C. Nguyen

11/18/08

17



[Zaman, Ayazi, et al, MEMS'06]

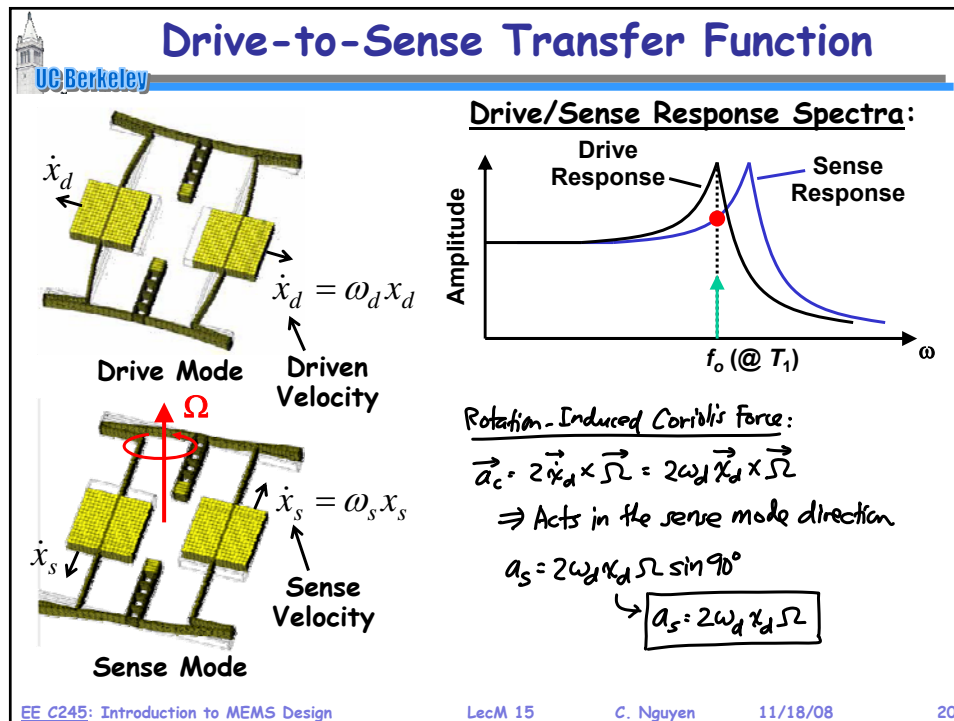
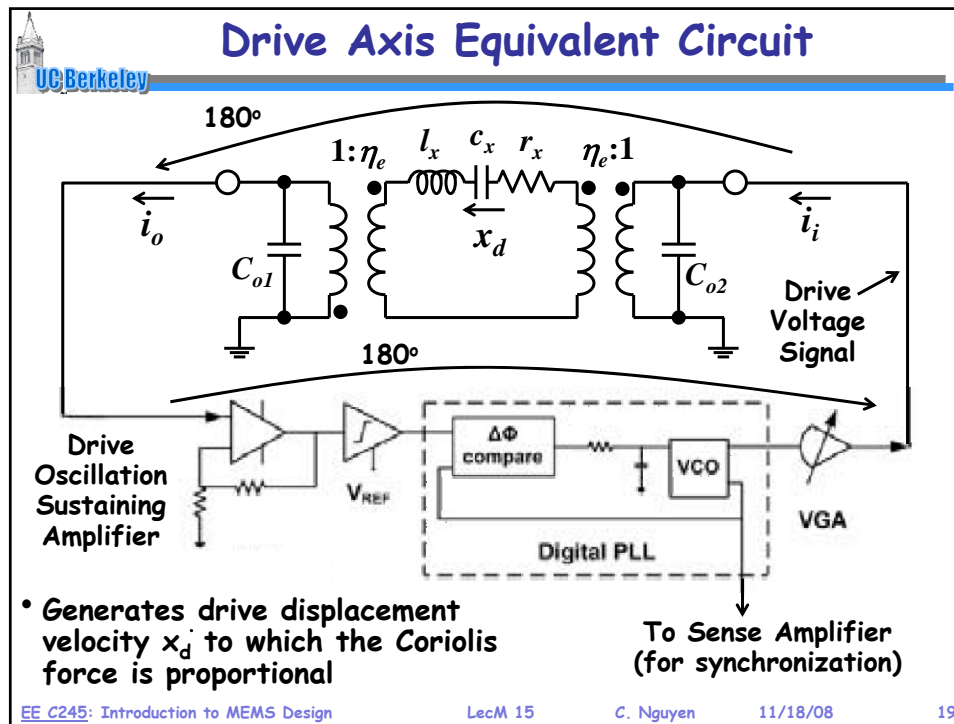
EE C245: Introduction to MEMS Design

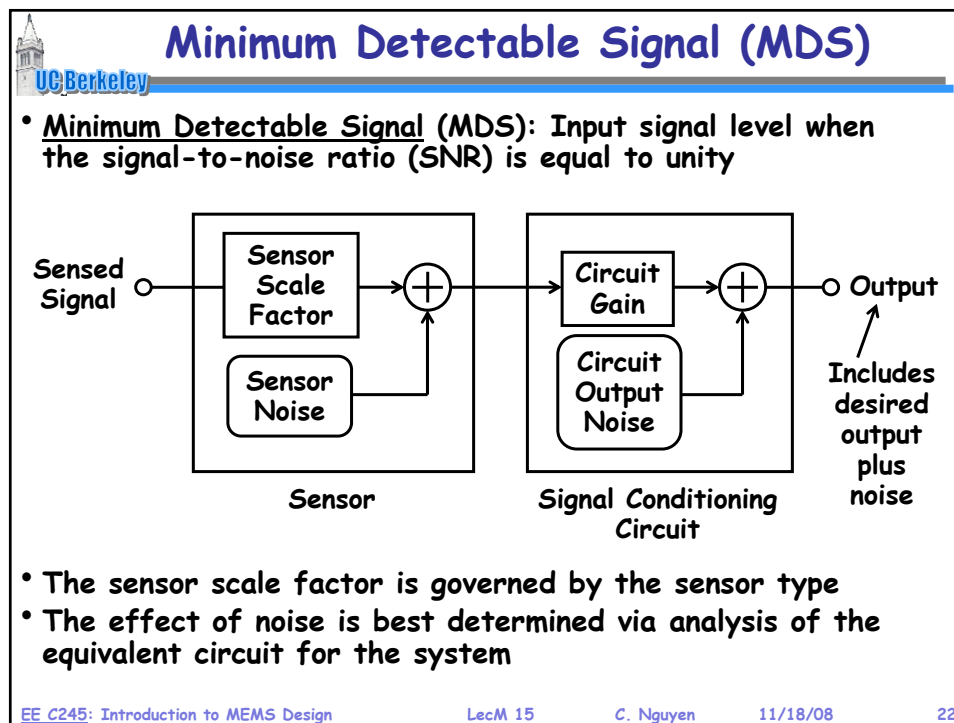
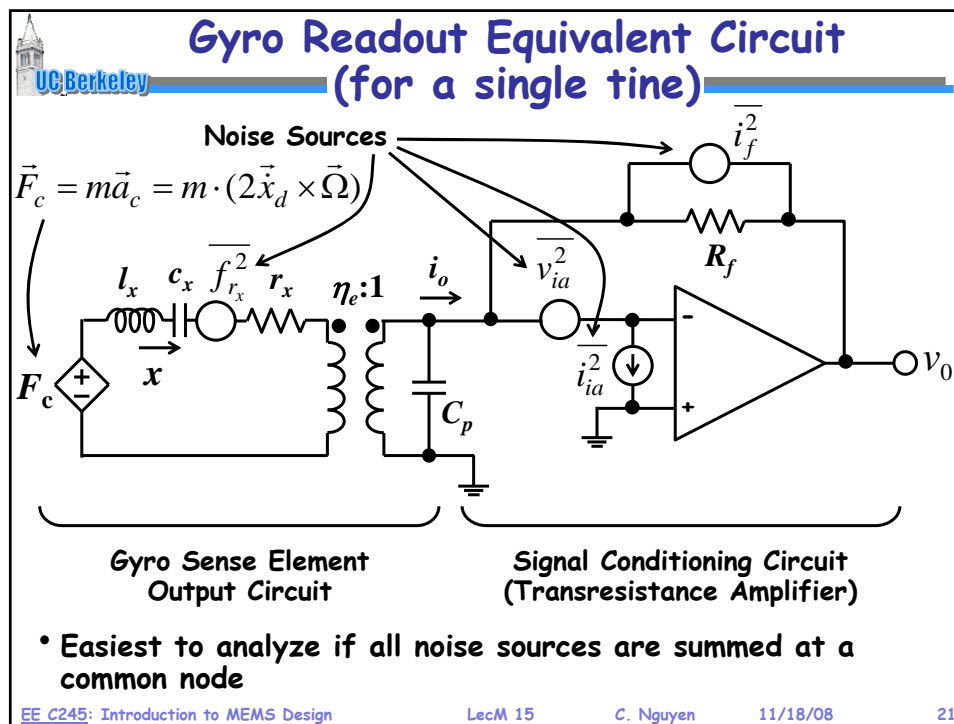
LecM 15

C. Nguyen

11/18/08

18





**Move Noise Sources to a Common Point**

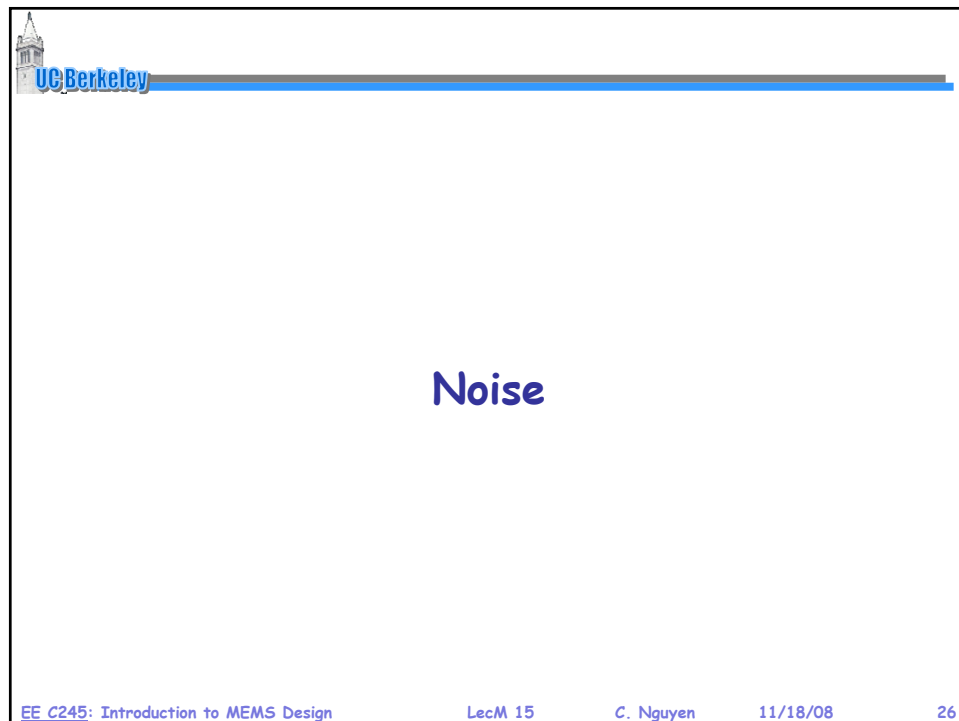
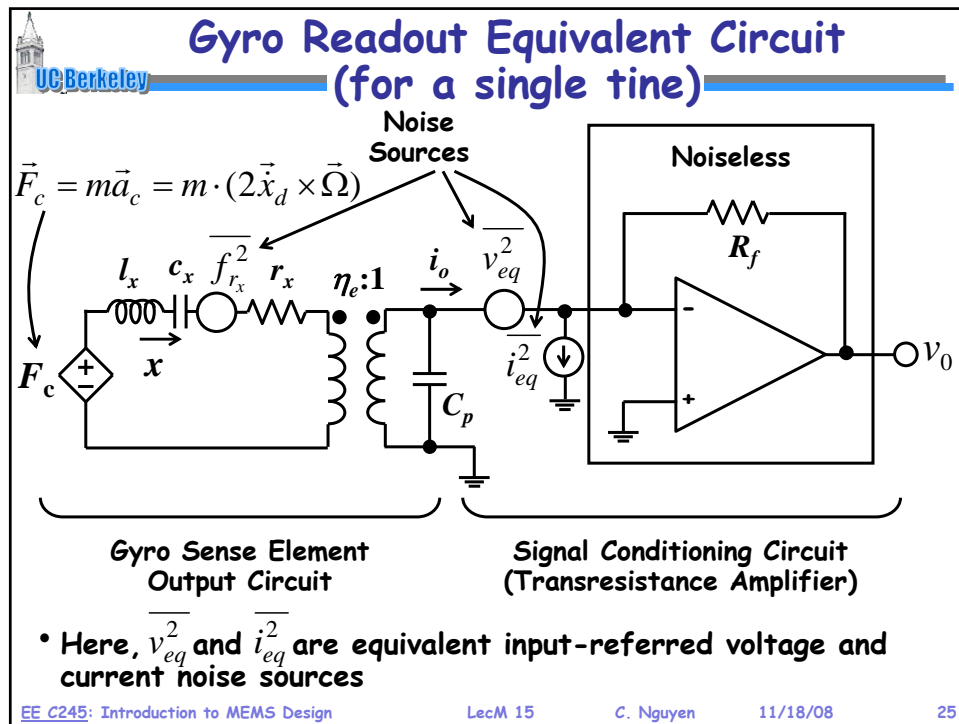
- Move noise sources so that all sum at the input to the amplifier circuit (i.e., at the output of the sense element)
- Then, can compare the output of the sensed signal directly to the noise at this node to get the MDS


EE C245: Introduction to MEMS Design      LecM 15      C. Nguyen      11/18/08      23

**Gyro Readout Equivalent Circuit (for a single time)**

• Easiest to analyze if all noise sources are summed at a common node

EE C245: Introduction to MEMS Design      LecM 15      C. Nguyen      11/18/08      24

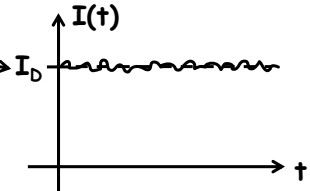




## Noise

- **Noise:** Random fluctuation of a given parameter  $I(t)$
- In addition, a noise waveform has a zero average value

Avg. value  
(e.g. could be  
DC current)




- We can't handle noise at instantaneous times
- But we can handle some of the averaged effects of random fluctuations by giving noise a power spectral density representation
- Thus, represent noise by its mean-square value:

Let  $i(t) = I(t) - I_D$

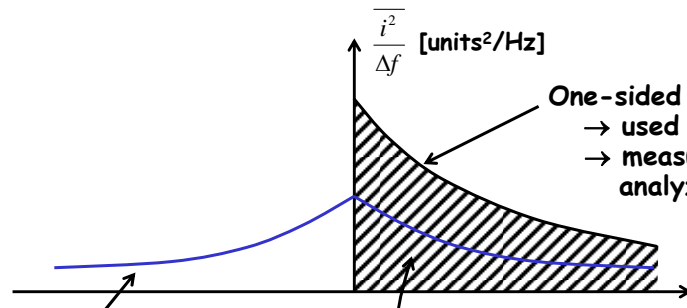
Then  $\overline{i^2} = \overline{(I - I_D)^2} = \lim_{T \rightarrow \infty} \frac{1}{T} \int_0^T |I - I_D|^2 dt$

EE C245: Introduction to MEMS Design
LecM 15
C. Nguyen
11/18/08
27



## Noise Spectral Density

- We can plot the spectral density of this mean-square value:



$\frac{\overline{i^2}}{\Delta f}$  [units<sup>2</sup>/Hz]

One-sided spectral density  
→ used in circuits  
→ measured by spectrum analyzers

Two-sided spectral density  
(1/2 the one-sided)

Often used in systems courses

$\overline{i^2} =$  integrated mean-square noise spectral density over all frequencies (area under the curve)

EE C245: Introduction to MEMS Design
LecM 15
C. Nguyen
11/18/08
28



### Circuit Noise Calculations

**Inputs**

$v_i(j\omega)$

$S_i(\omega)$

**Deterministic**

$H(j\omega)$

**Linear Time-Invariant System**

**Random**

**Outputs**

$v_o(j\omega)$

$S_o(\omega)$

*No  $j \rightarrow$  noise has random phase, so  $j$  is pointless!*

$v_o(t)$

$\frac{2\pi}{\omega_o}$

$v_o(j\omega)$

$\omega_o$

$S_o(t)$

$S_o(j\omega)$

$\omega_o$

Mean square spectral density

- Deterministic:**  $v_o(j\omega) = H(j\omega)v_i(j\omega)$
- Random:**  $S_o(\omega) = [H(j\omega)H^*(j\omega)]S_i(\omega) = |H(j\omega)|^2 S_i(\omega)$

$\sqrt{S_o(\omega)} = |H(j\omega)|\sqrt{S_i(\omega)}$ 

Root mean square amplitudes

How is it we can do this?

EE C245: Introduction to MEMS Design    LecM 15    C. Nguyen    11/18/08    29

### Handling Noise Deterministically

• Can do this for noise in a tiny bandwidth (e.g., 1 Hz)

$\frac{\overline{v_{n1}^2}}{\Delta f} = S_1(f) \rightarrow v_{n1} = \sqrt{S_1(f) \cdot B}$

Can approximate this by a sinusoidal voltage generator (especially for small B, say 1 Hz)

$S_n(j\omega)$

$\omega_o$

$v_o(t) = |A| \cos \omega_o t$

$\tau \sim \frac{1}{B}$

[This is actually the principle by which oscillators work → oscillators are just noise going through a tiny bandwidth filter]

Why? Neither the amplitude nor the phase of a signal can change appreciably within a time period 1/B.

EE C245: Introduction to MEMS Design    LecM 15    C. Nguyen    11/18/08    30

**Systematic Noise Calculation Procedure**

General Circuit With Several Noise Sources

• Assume noise sources are uncorrelated

1. For  $\overline{i_{n1}^2}$  replace w/ a deterministic source of value

$$i_{n1} = \sqrt{\frac{\overline{i_{n1}^2}}{\Delta f}} \cdot (1 \text{ Hz})$$

EE C245: Introduction to MEMS Design    LecM 15    C. Nguyen    11/18/08    31

**Systematic Noise Calculation Procedure**

2. Calculate  $v_{on1}(\omega) = i_{n1}(\omega)H(j\omega)$  (treating it like a deterministic signal)

3. Determine  $\overline{v_{on1}^2} = \overline{i_{n1}^2} \cdot |H(j\omega)|^2$

4. Repeat for each noise source:  $\overline{i_{n1}^2}, \overline{v_{n2}^2}, \overline{v_{n3}^2}$

5. Add noise power (mean square values)

$$\overline{v_{onTOT}^2} = \overline{v_{on1}^2} + \overline{v_{on2}^2} + \overline{v_{on3}^2} + \overline{v_{on4}^2} + \dots$$

$$v_{onTOT} = \sqrt{\overline{v_{on1}^2} + \overline{v_{on2}^2} + \overline{v_{on3}^2} + \overline{v_{on4}^2} + \dots}$$

↑  
Total rms value

EE C245: Introduction to MEMS Design    LecM 15    C. Nguyen    11/18/08    32

UC Berkeley

## Determining Sensor Resolution

EE C245: Introduction to MEMS Design      LecM 15      C. Nguyen      11/18/08      33

UC Berkeley

### Example: Gyro MDS Calculation

$\vec{F}_c = m\vec{a}_c = m \cdot (2\vec{\dot{x}}_d \times \vec{\Omega})$

The diagram illustrates a mechanical system (mass-spring-damper) connected to an electrical circuit. The mechanical system has mass  $m$ , spring constant  $k_x$ , and damping coefficient  $c_x$ . The displacement is  $x_s$ . The force  $F_c$  is applied. The system is connected to an amplifier circuit with feedback resistor  $R_f$  and a noiseless op-amp. The output voltage is  $v_0$ . The current  $i_o$  is the signal current, and  $i_{eq}$  is the equivalent current noise. The voltage noise  $v_{eq}^2$  is also shown.

- The gyro sense presents a large effective source impedance
  - ↳ Currents are the important variable; voltages are "opened" out
  - ↳ Must compare  $i_o$  with the total current noise  $i_{eqTOT}$  going into the amplifier circuit

EE C245: Introduction to MEMS Design      LecM 15      C. Nguyen      11/18/08      34

**Example: Gyro MDS Calculation (cont)**

UC Berkeley

$\vec{F}_c = m\vec{a}_c = m \cdot (2\vec{\dot{x}}_d \times \vec{\Omega})$

• First, find the rotation to  $i_o$  transfer function:

$$\dot{x}_s = \frac{\omega_s Q}{k_s} \Theta_s(j\omega_d) F_s = \frac{\omega_s Q}{k_s} \cdot 2\omega_d \chi_d \Omega m \cdot \Theta(j\omega_d)$$

$[F_s = F_c = 2\omega_d \chi_d \Omega m]$

$$\dot{x}_s = 2 \frac{\omega_d}{\omega_s} Q \chi_d \Theta(j\omega_d) \cdot \Omega$$

EE C245: Introduction to MEMS Design    LecM 15    C. Nguyen    11/18/08    35

**Example: Gyro MDS Calculation (cont)**

UC Berkeley

$i_o = \eta_e \dot{x}_s = 2 \frac{\omega_d}{\omega_s} Q \chi_d \eta_e \Theta(j\omega_d) \cdot \Omega \rightarrow i_o = A \Omega$

$A \triangleq \text{scale factor}$

Where  $A = 2 \frac{\omega_d}{\omega_s} Q \chi_d \eta_e \Theta(j\omega_d)$

When  $\Omega = \Omega_{\min} \triangleq \text{MDS}$ ,  $i_o = i_{eqTOT}$  ← input-referred noise current entering the sense amplifier → in pA/√Hz

$\therefore i_{eqTOT} = A \Omega_{\min} \rightarrow \Omega_{\min} = \frac{i_{eqTOT}}{A} \left( \frac{3600s}{hr} \right) \left( \frac{180^\circ}{\pi} \right) [(\%hr)/\sqrt{Hz}]$

Angle Random Walk:  $ARW = \frac{1}{60} \Omega_{\min} [^\circ/\sqrt{hr}]$

← Easier to determine directional error as a function of elapsed time.

EE C245: Introduction to MEMS Design    LecM 15    C. Nguyen    11/18/08    36

**Example: Gyro MDS Calculation (cont)**

UC Berkeley

$\vec{F}_c = m\vec{a}_c = m \cdot (2\vec{\dot{x}}_d \times \vec{\Omega})$

• Now, find the  $i_{eqTOT}$  entering the amplifier input:

$i_{eqTOT}^2 = i_s^2 + i_{eq}^2 \rightarrow i_{eqTOT}^2 = i_s^2 + i_f^2 + i_{ia}^2 + \frac{N_{ia}^2}{R_f^2}$   $\frac{f_{rx}^2}{\Delta f} = 4kTr_x$

Brownian motion noise of the sense element  $\rightarrow$  determined entirely by the noise in  $r_x \rightarrow \frac{f_{rx}^2}{\Delta f}$

$\rightarrow$  easiest to convert to an all electrical equiv. ckt.

EE C245: Introduction to MEMS Design LecM 15 C. Nguyen 11/18/08 37

**Example: Gyro MDS Calculation (cont)**

UC Berkeley

Where  $L_x = \frac{R_x}{\eta_e}$ ,  $C_x = \eta_e^2 C_x$ ,  $R_x = \frac{r_x}{\eta_e}$

$\therefore i_s = \sqrt{N_{R_x}} \left( \frac{1}{R_x} \right) \odot(j\omega_d) \rightarrow \frac{i_s^2}{\Delta f} = 4kTR_x \left( \frac{1}{R_x^2} \right) |\odot(j\omega_d)|^2$

$\Rightarrow \frac{i_s^2}{\Delta f} = \frac{4kT}{R_x} |\odot(j\omega_d)|^2$

Thus:

$\frac{i_{eqTOT}^2}{\Delta f} = \frac{4kT}{R_x} |\odot(j\omega_d)|^2 + \frac{4kT}{R_f} + \frac{i_{ia}^2}{\Delta f} + \frac{N_{ia}^2}{\Delta f} \left( \frac{1}{R_f^2} \right)$

Learn to get there from EE240.  
 $\rightarrow$  or just get them from a data sheet ...

EE C245: Introduction to MEMS Design LecM 15 C. Nguyen 11/18/08 38

## LF356 Op Amp Data Sheet

UC Berkeley

### LF155/LF156/LF256/LF257/LF355/LF356/LF357 JFET Input Operational Amplifiers

#### General Description

These are the first monolithic JFET input operational amplifiers to incorporate well matched, high voltage JFETs on the same chip with standard bipolar transistors (BI-FET™ Technology). These amplifiers feature low input bias and offset currents/low offset voltage and offset voltage drift, coupled with offset adjust which does not degrade drift or common-mode rejection. The devices are also designed for high slew rate, wide bandwidth, extremely fast settling time, low voltage and current noise and a low 1/f noise corner.

#### Features

##### Advantages

- Replace expensive hybrid and module FET op amps
- Rugged JFETs allow blow-out free handling compared with MOSFET input devices
- Excellent for low noise applications using either high or low source impedance—very low 1/f corner
- Offset adjust does not degrade drift or common-mode rejection as in most monolithic amplifiers
- New output stage allows use of large capacitive loads (5,000 pF) without stability problems
- Internal compensation and large differential input voltage capability

##### Applications

- Precision high speed integrators
- Fast D/A and A/D converters
- High impedance buffers
- Wideband, low noise, low drift amplifiers

#### Common Features

- Logarithmic amplifiers
- Photocell amplifiers
- Sample and Hold circuits
- Low input bias current: 30pA
- Low Input Offset Current: 3pA
- High input impedance:  $10^{12}\Omega$
- Low input noise current:  $0.01 \text{ pA}/\sqrt{\text{Hz}}$
- High common-mode rejection ratio: 100 dB
- Large dc voltage gain: 106 dB

#### Uncommon Features

	LF155/ LF355	LF156/ LF256/ LF356	LF257/ LF357 ( $A_V=5$ )	Units
■ Extremely fast settling time to 0.01%	4	1.5	1.5	$\mu\text{s}$
■ Fast slew rate	5	12	50	V/ $\mu\text{s}$
■ Wide gain bandwidth	2.5	5	20	MHz
■ Low input noise voltage	20	12	12	$\text{nV}/\sqrt{\text{Hz}}$

*Handwritten notes:*  
 $\sqrt{\frac{i_{ia}^2}{\Delta f}} = 0.01 \text{ pA}/\sqrt{\text{Hz}}$   
 $\sqrt{\frac{v_{ia}^2}{\Delta f}} = 12 \text{ nV}/\sqrt{\text{Hz}}$

8/08 39

## Example ARW Calculation

UC Berkeley

### • Example Design:

#### ↪ Sensor Element:

$$m = (100\mu\text{m})(100\mu\text{m})(20\mu\text{m})(2300\text{kg}/\text{m}^3) = 4.6 \times 10^{-10} \text{ kg}$$

$$\omega_s = 2\pi(15\text{kHz})$$

$$\omega_d = 2\pi(10\text{kHz})$$

$$k_s = \omega_s^2 m = 4.09 \text{ N/m}$$

$$x_d = 20 \mu\text{m}$$

$$Q_s = 50,000$$

$$V_p = 5\text{V}$$

$$h = 20 \mu\text{m}$$

$$d = 1 \mu\text{m}$$

#### ↪ Sensing Circuitry:


$$R_f = 100\text{k}\Omega$$

$$i_{ia} = 0.01 \text{ pA}/\sqrt{\text{Hz}}$$

$$v_{ia} = 12 \text{ nV}/\sqrt{\text{Hz}}$$

40



 **Example ARW Calculation (cont)**

Get rotation rate to output current scale factor:

$$A = 2 \frac{\omega_d}{\omega_s} Q_s \eta_e |H(j\omega_d)| = 2 \left( \frac{10k}{15k} \right) (50k) (20\mu) (5) (2000\epsilon_0) (0.000024) = 2.83 \times 10^{-12} C$$

$$\left[ H(j\omega_d) = \frac{(j\omega_d)(\omega_s/Q_s)}{-\omega_d^2 + \frac{j\omega_d\omega_s}{Q_s} + \omega_s^2} = \frac{j(10k)(15k)/(50k)}{(15k)^2 - (10k)^2 + \frac{j(10k)(15k)}{50k}} = \frac{j(3k)}{1.25 \times 10^8 + j(3k)} \right]$$

$$\Rightarrow |H(j\omega_d)| = \frac{3k}{\sqrt{(1.25 \times 10^8)^2 + (3k)^2}} = 0.000024 \quad 8.854 \times 10^{-8} F/m$$


$$\left[ \frac{\partial C}{\partial x} = \frac{C_0}{d} = \frac{\epsilon_0 h \omega_p}{d} = \frac{\epsilon_0 (20\mu)(100\mu)}{(1\mu)^2} = 2000\epsilon_0 \rightarrow \eta_e = V_p \frac{\partial C}{\partial x} = 5(2000\epsilon_0) \quad 8.854 \times 10^{-12} F/m \right]$$

Assume electrode covers the whole sidewall.

Then, get noise:

$$\frac{\overline{i_{eqTOT}^2}}{\Delta f} = \frac{4kT}{R_x} |H(j\omega_d)|^2 + \frac{4kT}{R_f} + \frac{\overline{i_{ia}^2}}{\Delta f} + \frac{\overline{N_{ie}^2}}{\Delta f} \left( \frac{1}{R_f} \right)$$

EE C245: Introduction to MEMS Design    LecM 15    C. Nguyen    11/18/08    41

 **Example ARW Calculation (cont)**

$$\left[ R_x = \frac{\omega_s m}{Q_s \eta_e^2} = \frac{2\pi(15k)(4.6 \times 10^{-10})}{(50k)(8.854 \times 10^{-8})^2} = 110.6 k\Omega \right]$$

$$\frac{\overline{i_{eqTOT}^2}}{\Delta f} = \frac{(1.66 \times 10^{-29})}{(110.6k)} (0.000024)^2 + \frac{(1.66 \times 10^{-29})}{1M} + (0.01p)^2 + \frac{(12n)^2}{(1M)^2}$$

$\rightarrow 8.64 \times 10^{-35} A^2/Hz$  (Sensor element noise, Insignificant)  
 $\uparrow$  Noise from  $R_f$  dominates!  
 $1.66 \times 10^{-26} A^2/Hz$   
 $1 \times 10^{-28} A^2/Hz$   
 $1.44 \times 10^{-28} A^2/Hz$

$$\therefore \frac{\overline{i_{eqTOT}^2}}{\Delta f} = 1.68 \times 10^{-26} A^2/Hz \rightarrow i_{eqTOT} = \sqrt{\frac{\overline{i_{eqTOT}^2}}{\Delta f}} = 1.30 \times 10^{-13} A/\sqrt{Hz}$$

$$\therefore \Omega_{min} = \frac{i_{eqTOT}}{A} \left( \frac{3600s}{hr} \right) \left( \frac{180^\circ}{\pi} \right) = \frac{1.30 \times 10^{-13}}{2.83 \times 10^{-12}} (3600) \left( \frac{180}{\pi} \right) = 9448 (\%hr)/\sqrt{Hz}$$

And finally:

$$ARW = \frac{1}{60} \Omega_{min} = \frac{1}{60} (9448) = 157 \%hr = ARW \Rightarrow \text{Almost turned around in 1 hour!}$$

EE C245: Introduction to MEMS Design    LecM 15    C. Nguyen    11/18/08    42

**What if  $\omega_d = \omega_s$ ?**

UC Berkeley

If  $\omega_d = \omega_s = 15\text{kHz}$ , then  $|\Phi(j\omega_d)| = 1$  and

$$A = 2 \frac{\omega_d}{\omega_s} Q_s X_d \eta_e |\Phi(j\omega_d)| = 2 Q_s X_d \eta_e = 2(50k)(20\mu)(5)(2000\epsilon_0) = 1.77 \times 10^{-7} \text{C}$$

$$\frac{\overline{i_{eqTOT}^2}}{\Delta f} = \frac{(1.66 \times 10^{-29})}{(110.6k)} (1)^2 + \frac{(1.66 \times 10^{-29})}{1M} + \underbrace{(0.01p)^2}_{1 \times 10^{-28} \text{A}^2/\text{Hz}} + \underbrace{\frac{(12n)^2}{(1M)^2}}_{1.44 \times 10^{-28} \text{A}^2/\text{Hz}}$$

$1.51 \times 10^{-25} \text{A}^2/\text{Hz}$      $1.66 \times 10^{-26} \text{A}^2/\text{Hz}$

Now, the sensor element dominates!

$$\therefore \frac{\overline{i_{eqTOT}^2}}{\Delta f} = 1.67 \times 10^{-25} \text{A}^2/\text{Hz} \rightarrow i_{eqTOT} = \sqrt{\frac{\overline{i_{eqTOT}^2}}{\Delta f}} = 4.08 \times 10^{-13} \text{A}/\sqrt{\text{Hz}}$$

$$\therefore S_{2min} = \frac{i_{eqTOT}}{A} \left( \frac{3600s}{hr} \right) \left( \frac{180^\circ}{\pi} \right) = \frac{4.08 \times 10^{-13}}{1.77 \times 10^{-7}} (3600) \left( \frac{180}{\pi} \right) = 0.476 (\%/hr)/\sqrt{\text{Hz}}$$

And finally:

$$ARW = \frac{1}{60} S_{2min} = \frac{1}{60} (0.476) = 0.0079 \%/hr = ARW \Rightarrow \text{Navigation grade!}$$

EE C245: Introduction to MEMS Design    LecM 15    C. Nguyen    11/18/08    43